



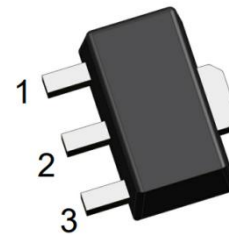
SSCND882GS3

NPN Plastic-Encapsulate Transistors

➤ Description

This product has the characteristics of high current and high-power consumption. It is universal and suitable for many different applications. It can be used for power amplifiers and switches that require collector currents up to 3A.

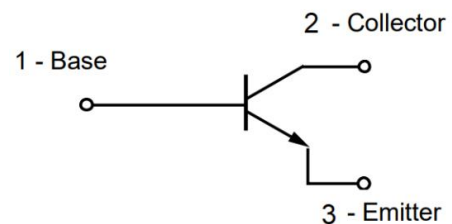
➤ Pin configuration



SOT-89-3L

➤ Features

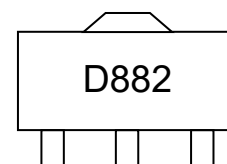
- Driver stages of audio amplifiers
- Linear voltage regulators
- Low-side switches
- Battery-driven devices
- Power management
- MOSFET drivers



Circuit Diagram

➤ Ordering Information

Device	Package	Shipping
SSCND882GS3	SOT-89	1000/Reel



Marking (Top View)



➤ **Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)**

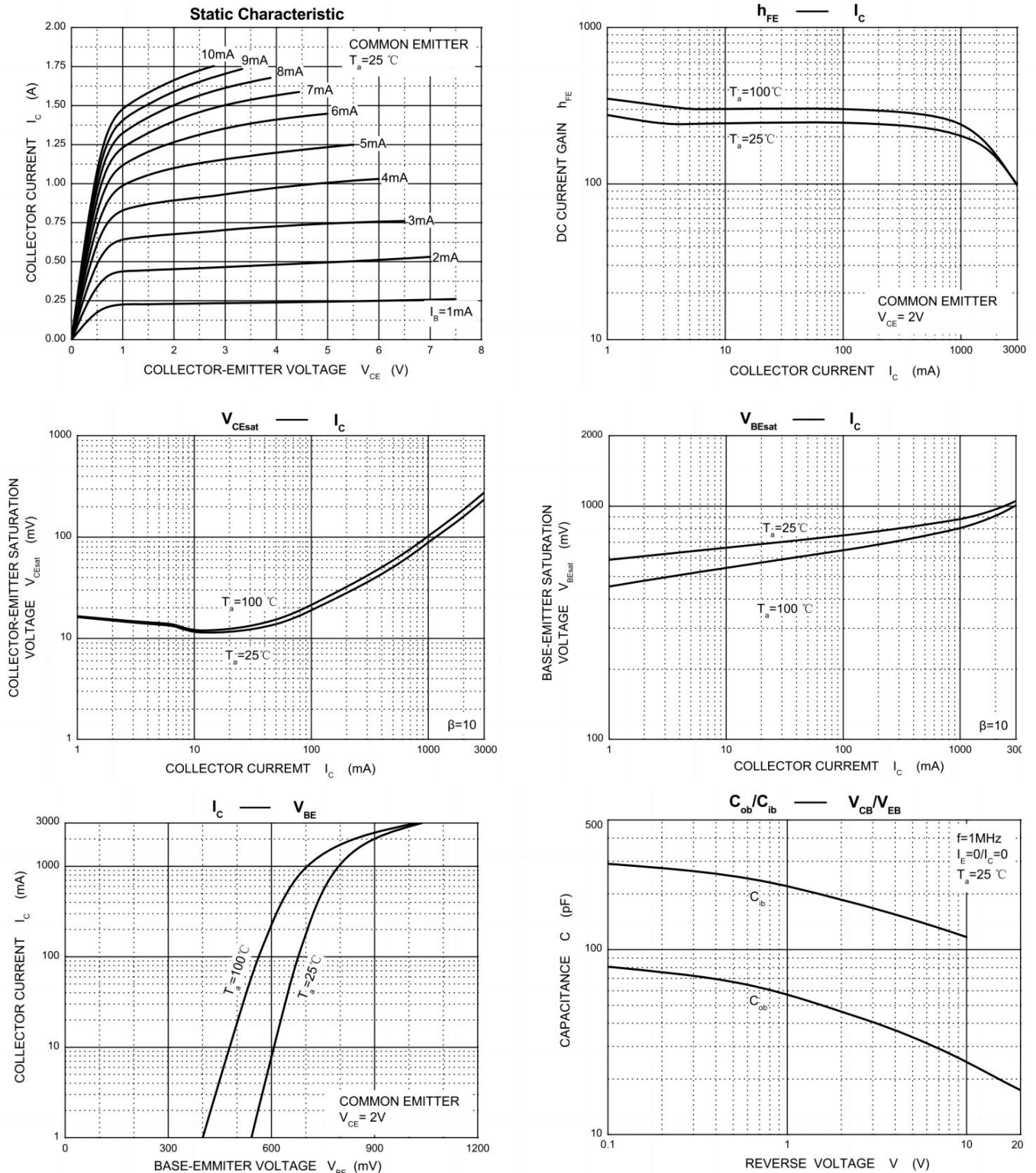
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector- Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current-Continuous	I_C	3	A
Collector Power Dissipation	P_C	500	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	250	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	-55 to 150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}\text{C}$

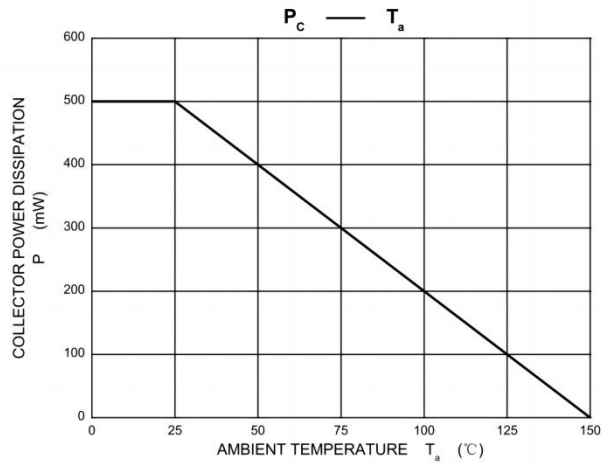
➤ **Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = 100\mu\text{A}$, $I_E = 0$	40			V
Collector-emitter Breakdown Voltage	BV_{CEO}	$I_C = 10\text{mA}$, $I_B = 0$	30			V
Emitter -Base Breakdown Voltage	BV_{EBO}	$I_E = 100\mu\text{A}$, $I_C = 0$	6			V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 40\text{V}$, $I_E = 0$			1.0	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 30\text{V}$, $I_E = 0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 6\text{V}$, $I_C = 0$			1.0	μA
DC Current Gain	h_{FE1}	$V_{CE} = 2\text{V}$, $I_C = 1.0\text{A}$	60		400	
DC Current Gain	H_{FE2}	$V_{CE} = 2\text{V}$, $I_C = 100\text{mA}$	32			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 2\text{A}$, $I_B = 200\text{mA}$			0.5	V
Base-Emitter Voltage	$V_{BE(sat)}$	$I_C = 2\text{A}$, $I_B = 200\text{mA}$			1.5	V
Transition frequency	f_T	$V_{CE} = 5\text{V}$, $I_C = 100\text{mA}$ $f = 10\text{MHz}$	50			MHz

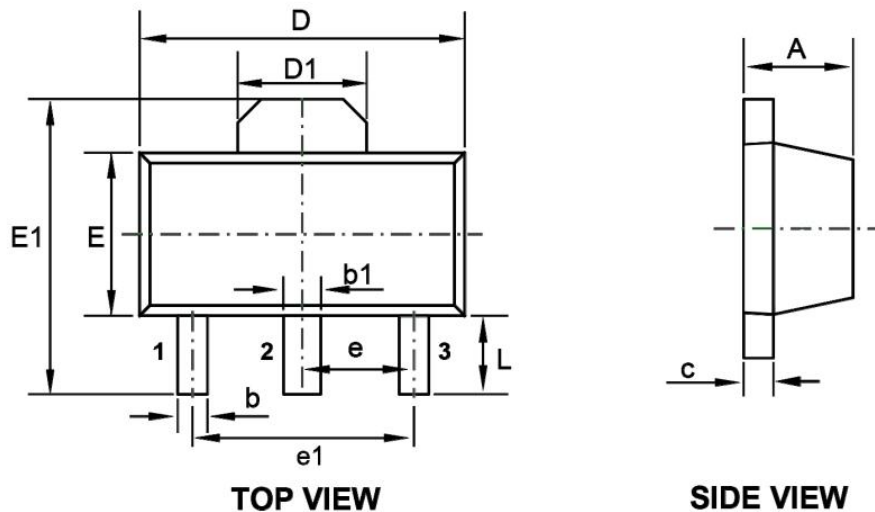


➤ Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)





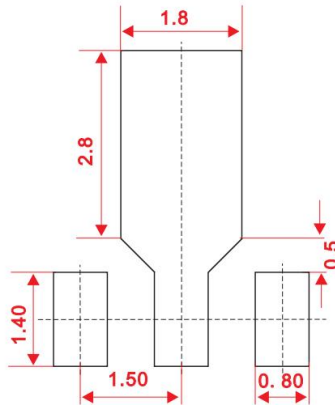
➤ Package Information



DIM	Millimeters		
	Min.	Typ.	Max.
A	1.40	-	1.60
b	0.32	-	0.52
b1	0.40	-	0.58
c	0.35	-	0.44
D	4.40	-	4.60
D1	1.55 REF.		
E	2.30	-	2.60
E1	3.94	-	4.25
e		1.50	
e1		3.00	
L	0.90	-	1.20



- Recommended Pad outline (Unit: mm)



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